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metal, and wherein the reflectance correlation uses said metal as a secondary film only to correlate, and trigger an endpoint on the substrate as a primary film being etched, wherein an output being monitored for endpoint detection is not physically representing the primary film being etched.

b3 b4 12. (Amended) A method of etching a material, comprising:

2 measuring a reflectance signal from a correlation material that is removed from the
3 path of a second material that is to be etched as the second material is etched;
4 correlating the second material etch rate to the reflectance signal from the correlation
5 material; and
6 using the etch ratio between the correlation material and the second material to
7 determine the etch target,
8 wherein said correlation material is isolated from an etching process.

b3 b4 18. (Amended) The method of claim 12, wherein said second material etch also etches a metal oxide on said metal, and wherein a thin film reflectance correlation uses said metal as a secondary film only to correlate, and trigger an endpoint on the second material as a primary film being etched,

wherein an output being monitored for endpoint detection is not physically representing the primary film being etched.

b5 b6 23. (Amended) A method of etching a semiconductor substrate, comprising:

2 measuring a reflectance signal from an opaque material deposited on said
3 semiconductor substrate as the semiconductor substrate is being etched;
4 correlating the semiconductor substrate etch rate to the reflectance signal from the
5 opaque material; and
6 using the etch relation between the semiconductor substrate and the opaque material
7 to determine the etch target,
8 wherein said opaque material is isolated from an etching process.

b6 b7 29. (Amended) The method of claim 23, wherein said opaque material comprises metal

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having a metal oxide thereon, and said substrate etch also etches said metal oxide on said metal, and wherein the reflectance correlation uses said metal as a secondary film only to correlate, and trigger an endpoint on the substrate as a primary film being etched,

wherein an output being monitored for endpoint detection is not physically representing the primary film being etched.

C **Please add the following new claims.** *C*

- 31. The method of claim 8, wherein a reflectivity of said metal and a reflectivity of said anti-reflective metal oxide are different.
- D1* 32. The method of claim 19, wherein a reflectivity of said metal and a reflectivity of said anti-reflective metal oxide are different.
- 33. The method of claim 30, wherein a reflectivity of said metal and a reflectivity of said anti-reflective metal oxide are different. --